

## 12. MISCELLANEOUS DIODES

IN ORDER OF (1) USE  
and (2) TYPE No.

LINE No.	TYPE No.	U S E	DESCRIPTION		TECHNICAL DATA
			MAT.	DWG. No.	
1	HP5082-0023	10		u19h	X-Band Mixer;Tangential Sensitivity -54dBm;CO 18pF at VR 0V, f 1MHz.
2	HP5082-0024	10		u19k	Switching Speed 100pS;Min VBR 70V at 10uA;Max VF 1.0V at 15mA;Max Co 1.7pF.
3	HP5082-0029	10		u19m	Ku-Band Mixer;Tangential Sensitivity -54dBm;CO 14pF at VR 0V, f 1MHz.
4	HP5082-0031	10		u19m	Switching Speed 100pS;Min VBR 5V at 100uA;Max VF 34V at 1.0mA;Max Co 8pF.
5	HP5082-0057	10		u19j	Chip for Hybrid IC Gen Purpose Ckts;VBR 20V min;IF 35mA min at VF 1.0V;Cj 1.0pf max
6	HP5082-0058	10		u19i	Chip for Hybrid IC Gen Purpose Ckts;VBR 15V min;IF 20mA min at VF 1.0V;Cj 1.0pf max
7	HP5082-0087	10		u19i	Switching Speed 100pS;Min VBR 20V at 10uA;Max VF 1.0V at 35mA;Max Co 1.0pf
8	HP5082-0094	10		u19k	Chip for Hybrid IC Gen Purpose Ckts;VBR 70V min;IF 15mA min at VF 1.0V;Cj 1.7pf max
9	HP5082-0097	10		u19j	Switching Speed 100pS;Min VBR 15V at 10uA;Max VF 1.0V at 20mA;Max Co 1.1pf.
10	HP5082-2229	10	Si#	A346	Mix-Det;Freq Rng 1-18GHz;CW Diss 300mW;VBR 3.0V min;VF 1.0V at 30mA;CT 25pF;NF6.0dB;SWR 1.5
11	HP5082-2231	10	Si	M845	Quad-Mixer;Freq Rng 1-4GHz;CW Diss 75mW;CT 6pf;VF 300mV at 1mA;RS 5.00;Tj 125°
12	HP5082-2233	10	Si	M845	Quad-Mixer;Freq Rng 4-8GHz;CW Diss 75mW;CT 35pf;VF 300mV at 1mA;RS 7.00;Tj 150°
13	HP5082-2261	10		M845	Quad-Mixer;CT 600f max;ACT 100f max;AVF 20mV max;Freq RG to 4GHz;VF 400mV typ;RS 7Ω typ.
14	HP5082-2263	10		M845	Quad-Mixer;CT 350f max;ACT 50f max;AVF 20mV max;Freq RG 8-8GHz;VF 450mV typ;RS 7Ω typ.
15	HP5082-2264	10	Si#	A346	Mix-Det;Freq Rng 1-18GHz;CW Diss 300mW;VBR 3.0V min;VF 1.0V at 15mA;CT 15pF;NF6.0dB;SWR 1.5
16	HP5082-2271	10	Si	M846	Quad-Mixer;Freq Rng 1-4GHz;CW Diss 75mW;CT 6pf;VF 300mV at 1mA;RS 5.00;Tj 125°
17	HP5082-2272	10	Si	M846	Quad-Mixer;Freq Rng 4-8GHz;CW Diss 75mW;CT 45pf;VF 300mV at 1mA;RS 7.00;Tj 125°
18	HP5082-2276	10		M895	Quad-Mixer;Freq Rng 2-4GHz;DC Pd 75mW(per junc);CT 60pF max;VF 40V typ;Rs 10Ω typ
19	HP5082-2277	10		M895	Quad-Mixer;Freq Rng 4-8GHz;DC Pd 75mW(per junc);CT 50pF max;VF 45V typ;Rs 15Ω typ
20	HP5082-2279	10	Si	M846	Quad-Mixer;Freq Rng 8-12GHz;CW Diss 75mW;CT 25pf;VF 300mV at 1mA;RS 7.00;Tj 125°
21	HP5082-2280	10	Si	M846	Quad-Mixer;Freq Rng 12-18GHz;CW Diss 75mW;CT 17pf;VF 300mV at 1mA;RS 7.00;Tj 125°
22	HP5082-2291	10		M846	Quad-Mixer;CT 600f max;ACT 100f max;AVF 20mV max;Freq RG to 4GHz;VF 400mV typ;RS 7Ω typ.
23	HP5082-2292	10		M846	Quad-Mixer;CT 400f max;ACT 100f max;AVF 20mV max;Freq RG 4-8GHz;VF 400mV typ;RS 7Ω typ.
24	HP5082-2293	10		M846	Quad-Mixer;CT 250f max;ACT 50f max;AVF 20mV max;Freq RG 8-12GHz;VF 450mV typ;RS 7Ω typ.
25	HP5082-2294	10		M846	Quad-Mixer;CT 200f max;ACT 50f max;AVF 20mV max;Freq RG 12-18GHz;VF 450mV typ;RS 7Ω typ.
26	HP5082-2298	10	Si#	A346	Mix-Det;Freq Rng 1-18GHz;CW Diss 300mW;VBR 3.0V min;VF 1.0V at 20mA;CT 15pF;NF6.0dB;SWR 1.5
27	HP5082-2705	10		u12	X-Band Det/Mix;Tss-54dBm at 10GHz;Mix NF 6dB typ at 9.375GHz;Cj 0.18pf max at 0V,1.0MHz
28	HP5082-2710	10		M791	X-Band Det/Mix;Tss-54dBm at 10GHz;Mix NF 7dB typ at 9.375GHz;Cj 0.14pf max at 0V,1.0MHz
29	HP5082-2753	10		M791	X-Band Det/Mix;Tss-54dBm at 10GHz;Mix NF 7dB typ at 9.375GHz;Cj 0.14pf max at 0V,1.0MHz
30	HP5082-2754	10		u12	X-Band Det/Mix;Tss-54dBm at 10GHz;Mix NF 7dB typ at 9.375GHz;Cj 0.14pf max at 0V,1.0MHz
31	HP5082-2800	10	#	A1nΔ	VBR 70V min;VF 410mV max;Ir 200mA max;Cap 2.0pf max;Carrier Lifetime 100ps max.
32	HP5082-2801	10	#	M791	Switching Speed 100pS;Min VBR 70V at 10uA;Max VF 1.0V at 15mA;Max Co 2.0pF.
33	HP5082-2802	10	#	u12	Switching Speed 100pS;Min VBR 70V at 10uA;Max VF 1.0V at 15mA;Max Co 2.0pF.
34	HP5082-2810	10	#	A1n	VBR 20V min;VF 410mV max;Ir 100mA max;Cap 1.2pf max;Carrier Lifetime 100ps max.
35	HP5082-2811	10	#	A1n	VBR 15V min;VF 410mV max;Ir 100mA max;Cap 1.2pf max;Carrier Lifetime 100ps max.
36	HP5082-2830	10	Si	M491g	Quad-Mixer;Max Freq 2GHz;CW Diss 75mW(per junc);ΔCj 20pf max;VF 4V typ at 1mA;Rs 7Ω typ
37	HP5082-2831	10	Si	M491g	Quad-Mixer;Max Freq 2GHz;CW Diss 75mW(per junc);ΔCj 20pf max;VF 25V typ at 1mA;Rs 7Ω typ
38	HP5082-2837	10		A330	Switching Speed 100pS;Min VBR 70V at 10uA;Max VF 1.0V at 15mA;Max Co 2.0pF.
39	HP5082-2844	10		u12	Switching Speed 100pS;Min VBR 15V at 10uA;Max VF 1.0V at 20mA;Max Co 1.4pF.
40	HP5082-2845	10		M791	Switching Speed 100pS;Min VBR 15V at 10uA;Max VF 1.0V at 20mA;Max Co 1.4pF.
41	MA4850	10	Si	A1ad	Broad Band Mixer;f3060Mc;Zif at 1.0mW-125-250 ohms;Ct-1.0pF;NF-9.0dB.
42	MA4851	10	Si	A1adΔ	Broad Band Mixer;f3060Mc;Zif at 1.0mW-125-250 ohms;Ct-7.0pF;NF-7.5dB.
43	MA4852	10	Si	A1adΔ	Broad Band Mixer;f3060Mc;Zif at 1.0mW-125-250 ohms;Ct-5.0pF;NF-6.5dB.
44	MA4853	10	Si	A1adΔ	Broad Band Mixer;f3060Mc;Zif at 1.0mW-125-250 ohms;Ct-5.0pF;NF-5.5dB.
45	MA4854	10	Si	A1ad	Broad Band Mixer;f3060Mc;Zif at 1.0mW-125-250 ohms;Ct-5.0pF;NF-5.0dB.
46	MA4855	10	Si	A1adΔ	Broad Band Mixer;f9375Mc;Zif at 1.0mW 200-400Ω;NF 8.5dB.
47	MA4856	10	Si	A1adΔ	Broad Band Mixer;f9375Mc;Zif at 1.0mW 200-400Ω;NF 7.5dB.
48	MA4857	10	Si	A1adΔ	Broad Band Mixer;f9375Mc;Zif at 1.0mW 200-400Ω;NF 6.5dB.
49	MA4858	10	Si	A1adΔ	Broad Band Mixer;f9375Mc;Zif at 1.0mW 200-400Ω;NF 7.0dB.
50	MA4878	10	Si	A1ad	Pd-50mW;Ct-1.0pf max;VF-65V max. at If-20mA.
51	MA4882	10	Si	A1adΔ	Mixer;L-Band;Test ft-1.0GHz;Zif at 1.0mW 125-250Ω;NF 5.5dB.
52	MA4883	10	Si	A1adΔ	Mixer;L-Band;Test ft-1.0GHz;Zif at 1.0mW 125-250Ω;NF 6.5dB.
53	MA40401	10	GA	u14	Ka-Band Det/Mix;Tss-50dBm typ;Mixer NF 7.5dBmax at 36GHz;Cj 0.05pf typ;Rs 6.0Ω typ
54	MA40402	10	GA	P9a	Ka-Band Det/Mix;Tss-50dBm typ;Mixer NF 7.5dBmax at 36GHz;Cj 0.05pf typ;Rs 6.0Ω typ
55	MA40403	10	GA	M790	Ka-Band Det/Mix;Tss-50dBm typ;Mixer NF 7.5dBmax at 36GHz;Cj 0.05pf typ;Rs 6.0Ω typ
56	MA40406	10	GA	F105a	Ka-Band Det/Mix;Tss-50dBm typ;Mixer NF 7.5dBmax at 36GHz;Cj 0.05pf typ;Rs 6.0Ω typ
57	MA40408	10	GA	†	60GHz Det/Mix;Tss-48dBm;Mixer NF 8.5dB at 60GHz;Cj 0.04pf typ;Rs 7.5Ω typ
58	MA40409	10	GA	†	60GHz Det/Mix;Tss-48dBm;Mixer NF 8.5dB at 60GHz;Cj 0.04pf typ;Rs 7.5Ω typ
59	MA40410	10	GA	†	90GHz Det/Mix;Tss-45dBm;Mixer NF 10dB at 90GHz;Cj 0.005pf typ;Rs 9.0Ω typ
60	MA40412	10	GA	†	90GHz Det/Mix;Tss-45dBm;Mixer NF 10.5dB at 90GHz;Cj 0.005pf typ;Rs 9.0Ω typ
61	MBD102	10	Si	A276	Hot Carrier UHF Mixer;VR 4.0V;Pd 400mW;VF 480mV;Capacitance 800f;Inductance 3.0nH.
62	MBD201	10	Si	M764a	Hot-Carrier Detector;VR 20V;Pd 500mW;VF 600mVdc;CT 1.5pf;Carrier Lifetime 100ps.
63	MBD301	10	Si	M764a	Hot-Carrier Detector;VR 30V;Pd 500mW;VF 600mVdc;CT 1.5pf;Carrier Lifetime 100ps.
64	MBD501	10	Si	C132	Hot carrier diode;VR 50V;Pd 500mW;Cap. 1.0pF max;Ir 200mA max;Carrier Lifet. 15ps.
65	MBD502	10	Si	A276	Hot Carrier Detector;VR 50V;Pd 400mW;VF 1.0V;Capacitance 480f;Rev. Leakage 7.0nA.
66	MBD701	10	Si	C132	Hot carrier diode;VR 70V;Pd 500mW;Cap. 1.0pF max;Ir 200mA max;Carrier Lifet. 15ps.
67	MBD702	10	Si	A276	Hot Carrier Detector;VR 70V;Pd 400mW;VF 1.0V;Capacitance 480f;Rev. Leakage 9.0nA.
68	MD358	10	Si	M785a	Beam Lead;V(BR)4.0V;VF 650mV at IF 10mA;CT 180f;Single Side Band NF 6.5dB.
69	MD3653	10	GA	M790a	Mixer;V(BR) 5.0V min;CJ 80f Typ;RS 5.0Ω Typ;Freq Rng 300MHz-40GHz;IF 20mA
70	MD3654	10	GA	M790a	Mixer;V(BR) 5.0V min;CJ 80f Typ;RS 5.0Ω Typ;Freq Rng 300MHz-40GHz;IF 20mA
71	MD3655	10	GA	M790a	Mixer;V(BR) 5.0V min;CJ 80f Typ;RS 5.0Ω Typ;Freq Rng 300MHz-40GHz;IF 20mA
72	MS114	10	Si		IF-10mA at VF-1.0V;Ct-80pf;PIV-10V at 10uA;Rs-35 ohms;Platinum Junction.
73	MS124	10	Si		IF-50mA at VF-1.0V;Ct-80pf;PIV-10V at 10uA;Rs-10 ohms;Platinum Junction.
74	MS134	10	Si		IF-100mA at VF-1.0V;Ct-80pf;PIV-10V at 10uA;Rs-3.5 ohms;Platinum Junction.
75	MS214	10	Si		IF-10mA at VF-1.0V;Ct-80pf;PIV-20V at 10uA;Rs-35 ohms;Platinum Junction.
76	MS224	10	Si		IF-50mA at VF-1.0V;Ct-80pf;PIV-20V at 10uA;Rs-10 ohms;Platinum Junction.
77	MS314	10	Si		IF-10mA at VF-1.0V;Ct-80pf;PIV-30V at 10uA;Rs-35 ohms;Platinum Junction.
78	MS324	10	Si		IF-50mA at VF-1.0V;Ct-80pf;PIV-30V at 10uA;Rs-10 ohms;Platinum Junction.
79	MS334	10	Si		IF-100mA at VF-1.0V;Ct-80pf;PIV-30V at 10uA;Rs-3.5 ohms;Platinum Junction.
80	MS514	10	Si		IF-10mA at VF-1.0V;Ct-80pf;PIV-50V at 10uA;Rs-35 ohms;Platinum Junction.
81	MS524	10	Si		IF-50mA at VF-1.0V;Ct-80pf;PIV-50V at 10uA;Rs-10 ohms;Platinum Junction.
82	MSJ112	10	Si		IF-10mA at VF-1.0V;Ct-80pf;PIV-5.0V at 10uA;Rs-50 ohms;Copper Junction.
83	MSJ114	10	Si		IF-10mA at VF-1.0V;Ct-80pf;PIV-5.0V at 10uA;Rs-35 ohms;Platinum Junction.
84	PF930B05	10	GA	F10af	Harm.Gen.Var;Min VB 30V;Min-Max Cj at zero bias and 1MHz 30-60pf;Min fc at 6V 250GHz.
85	PKK500	10	Si	A1ad	Max VF 400V at IF 1.0mA;Min IF 20mA at VF 1.0V;C to Max 1.0pf;Min Car Life 100ps.
86	PKK501	10	Si	A1ad	Max VF 400V at IF 1.0mA;Min IF 20mA at VF 1.0V;C to max 1.0pf;Min Car Life 100ps.
87	PKK502	10	Si	A1ad	Max VF 400V at IF 1.0mA;Min IF 20mA at VF 1.0V;C to max 1.0pf;Min Car Life 100ps.
88	PKK503	10	Si	A1ad	Max VF 400V at IF 1.0mA;Min IF 15mA at VF 1.0V;C to max 1.0pf;Min Car Life 100ps.
89	PKK504	10	Si	A1ad	Max VF 400V at IF 1.0mA;Min IF 15mA at VF 1.0V;C to max 1.0pf;Min Car Life 100ps.
90	SD-41	10	†	DO5	Max VF 550mV at 30Adc;Max IR 100mA at 35Vdc;Cj 2000pF max;Max Oper Temp 150°C
91	SD-51	10	†	S19ad	Max VF 600mV at 60Adc;Max IR 200mA at 35Vdc;Cj 4000pF max;Max Oper Temp 150°C
92	SSP310	10	†	DO4	IF 3.0A max;VBR 10V at 10mA;IR 25mA max at 7V,125°C;VF 60V max at IF 3.0A
93	SSP320	10	†	DO4	IF 3.0A max;VBR 20V at 10mA;IR 25mA max at 14V,125°C;VF 60V max at IF 3.0A
94	SSP330	10	†	DO4	IF 3.0A max;VBR 30V at 10mA;IR 25mA max at 21V,125°C;VF 60V max at IF 3.0A
95	SSP340	10	†	DO4	IF 3.0A max;VBR 40V at 10mA;IR 25mA max at 28V,125°C;VF 60V max at IF 3.0A
96	SSP350	10	†	DO4	IF 3.0A max;VBR 50V at 10mA;IR 25mA max at 35V,125°C;VF 60V max at IF 3.0A
97	SSP360	10	†	DO4	IF 3.0A max;VBR 60V at 10mA;IR 25mA max at 42V,125°C;VF 60V max at IF 3.0A
98	SSP370	10	†	DO4	IF 3.0A max;VBR 70V at 10mA;IR 25mA max at 49V,125°C;VF 60V max at IF 3.0A
99	SSP810	10	†	DO4	IF 8.0A max;VBR 10V at 10mA;IR 150mA max at 7V,125°C;VF 52V max at IF 8.0A
100	SSP820	10	†	DO4	IF 8.0A max;VBR 20V at 10mA;IR 150mA max at 14V,125°C;VF 52V max at IF 8.0A
101	SSP830	10	†	DO4	IF 8.0A max;VBR 30V at 10mA;IR 150mA max at 21V,125°C;VF 52V max at IF 8.0A
102	SSP840	10	†	DO4	IF 8.0A max;VBR 40V at 10mA;IR 125mA max at 28V,125°C;VF 54V max at IF 8.0A
103	SSP850	10	†	DO4	IF 8.0A max;VBR 50V at 10mA;IR 125mA max at 35V,125°C;VF 54V max at IF 8.0A
104	SSP860	10	†	DO4	IF 8.0A max;VBR 60V at 10mA;IR 125mA max at 42V,125°C;VF 54V max at IF 8.0A
105	SSP2010	10	†	DO4	IF 20A max;VBR 10V at 10mA;IR 150mA max at 7.5V,125°C;VF 46V max at IF 20A
106	SSP2020	10	†	DO4	IF 20A max;VBR 20V at 10mA;IR 150mA max at 15V,125°C;VF 46V max at IF 20A
107	SSP2030	10	†	DO4	IF 20A max;VBR 30V at 10mA;IR 150mA max at 22.5V,125°C;VF 50V max at IF 20A
108	SSP2040	10	†	DO4	IF 20A max;VBR 40V at 10mA;IR 125mA max at 30V,125°C;VF 52V max at IF 20A
109	SSP2050	10	†	DO4	IF 20A max;VBR 50V at 10mA;IR 125mA max at 37.5V,125°C;VF 52V max at IF 20A
110	SSP3005	10	†	DO5	IF 30A max;VBR 5.0V at 10mA;IR 150mA max at 5V,125°C;VF 54V max at IF 30A